

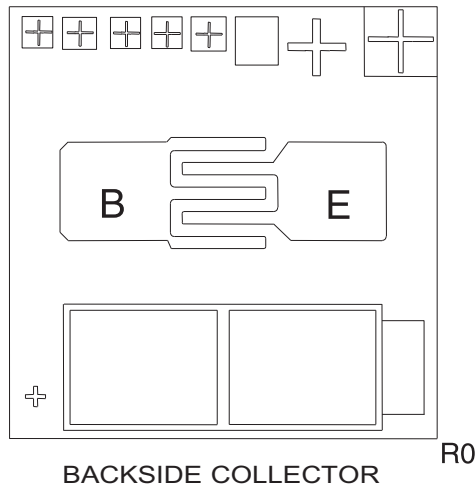
PROCESS CP317
Small Signal Transistor
 NPN - RF Transistor Chip



PROCESS DETAILS

Process	EPITAXIAL PLANAR
Die Size	14.5 x 14.5 MILS
Die Thickness	9.0 MILS
Base Bonding Pad Area	2.4 x 2.2 MILS
Emitter Bonding Pad Area	2.4 x 2.2 MILS
Top Side Metalization	Al - 30,000Å
Back Side Metalization	Au - 18,000Å

GEOMETRY



GROSS DIE PER 4 INCH WAFER

53,788

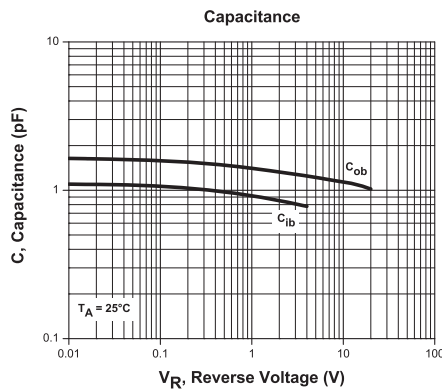
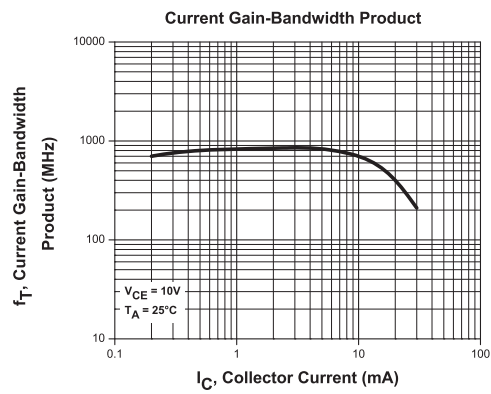
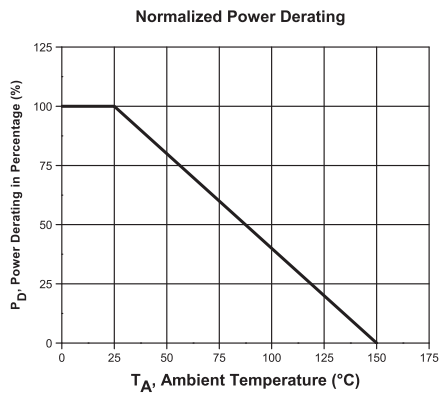
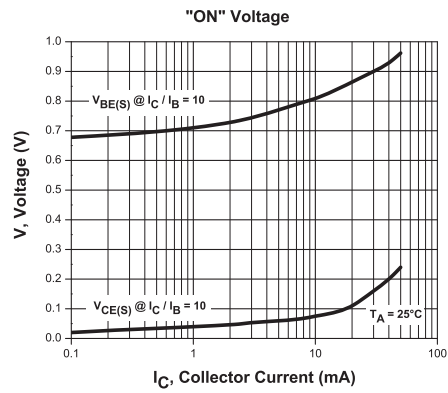
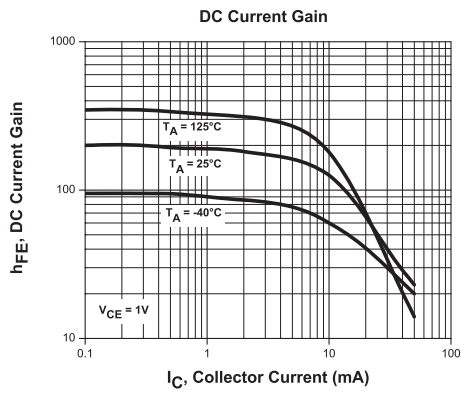
PRINCIPAL DEVICE TYPES

- CMPT918
- 2N918
- 2N2857
- 2N5179
- 2N5770
- BFY90
- PN3563
- PN3564

R3 (22-March 2010)

PROCESS CP317

Typical Electrical Characteristics



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